



Ain Shams University
Faculty of Engineering
Electronics and Communication Department

Design of Low Power Readout Circuit using FinFET Technology

A Thesis

Submitted in partial fulfillment of the requirements of a Master of Science
degree in Electrical Engineering

Submitted by:

Theodora Mamdouh Shehata Rezk
B.Sc. of Electrical Engineering
(Electronics and Communication Department)
Ain Shams University, 2010

Supervised by:

Prof. Hani Fikry Mohamed Ragai
Prof. Wagdy Refaat Anis
Dr. Diaa Eldin Khalil

Cairo, 2015



**Ain Shams University
Faculty of Engineering**

Name: **Theodora Mamdouh Shehata Rezk**

Thesis: **Design of Low Power Readout Circuit using FinFET Technology**

Degree: **Master of Science in Electrical Engineering(Electronics and Communication)**

Examiners Committee:

Name

Signature

Prof. Khaled Ali Shehata

Prof. Mohamed Amin Dessouky

Prof. Hani Fikry Mohamed Ragai

Prof. Wagdy Refaat Anis

Date: / / 2015

Statement

This thesis is submitted to Ain Shams University in partial fulfillment of the requirements for the degree of Master of Science in Electrical Engineering.

The author carried out the work included in this thesis, and no part of it has been submitted for a degree or qualification at any other scientific entity

Name: Theodora Mamdouh Shehata Rezk

Signature:

Date:

Curriculum Vitae

Name: Theodora Mamdouh Shehata Rezk

Date of Birth: 09/04/1988

Place of Birth: Cairo, Egypt

First Degree: B.Sc. in Electrical Engineering

Name of University: Ain Shams University

Date of Degree: June 2010

Summary

FinFET technology has been born as a result of the relentless increase in the levels of integration. The basic tenet of Moore's law has held true for many years from the earliest years of integrated circuit technology. Essentially it states that the number of transistors on a given area of silicon doubles every two years. FinFET technology takes its name from the fact that the FET structure used looks like a set of fins when viewed. The FinFET is a technology that is used in IC implementation. FinFETs are not available as discrete devices. However FinFET technology is becoming more widespread as feature sizes within integrated circuits shrink down and there is a growing need to provide very much higher levels of integration with less power consumption.

This thesis focuses on design of a capacitive pressure sensor readout circuit using the FinFET technology and comparing it with that based on traditional CMOS technology. FinFET-based design shows less power consumption in the proposed circuits.

The first chapter is an introductory chapter for the whole thesis, presenting the main concept and developing the thesis organization.

The second chapter gives a background on the sensor used in the thesis. It also present many architectures for the readout circuit allowing to choose a suitable circuit for the proposed readout circuit. A survey on low power techniques is also presented, as it is our main goal in the thesis; designing low power circuits.

The third chapter introduces the new FinFET device, it declares the need for a new technology, highlighting the advantages of using FinFET device in next technology generations. The FinFET technology is a good choice for low power circuits.

The fourth chapter proposes the readout circuit design, using two architecture to convert the capacitance of the sensor into frequency; LC and ring oscillators. The design of a counter stage needed to detect the resulting frequency is given in this chapter. Simulation of circuits using FinFET and CMOS 0.13 μm technology are presented with emphasis on the power dissipation in each technology.

The last chapter gives a comparative study between the results in this thesis and previous published work. Also a discussion is given and a conclusion is drawn.

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Contents

List of Figures	x
List of Tables	xiii
1 Introduction	1
1.1 Motivation	1
1.2 Organization	1
2 Background	2
2.1 Capacitive pressure sensor	2
2.2 Readout circuits	5
2.3 Low power techniques	11
2.3.1 Motivation for low power circuits	11
2.3.2 Sources of power dissipation	13
2.3.3 Challenges in low voltage low power design	14
2.3.4 Low power methodologies	16
3 FinFET Technology	21
3.1 Semiconductor technology beyond 22 nm	21
3.2 Multi gate MOSFET	23
3.2.1 FinFET performance	24
3.2.2 BSIM-CMG model used with 16 nm PTM model card	26
4 Proposed Design	33
4.1 Overall system	33
4.2 Pressure sensor	35
4.3 Oscillator design	37
4.3.1 Cross coupled LC oscillator	37
4.3.1.1 CMOS 0.13 μm design of the LC oscillator	38
4.3.1.2 FinFET design of the LC oscillator	41
4.3.2 Ring oscillator	44

4.3.2.1	CMOS 0.13 μm design of the ring oscillator . . .	45
4.3.2.2	Schematic simulation results	47
4.3.2.3	Layout and post layout simulation results . . .	49
4.3.2.4	FinFET design of the ring oscillator	54
4.3.2.5	FinFET tentative layout of the ring oscillator	57
4.4	Counter design	61
4.4.1	CMOS 0.13 μm design of the counter	64
4.4.2	FinFET design of the counter	64
4.5	Summary	67
5	Discussion and Conclusion	68
	Appendices	71
A	Verilog A code for the sensor	72
B	Predictive technology model used in simulation	74
	Bibliography	81

List of Figures

2.1	Sensor's cross sections	4
2.2	Square wave driven AC-bridge with voltage amplifier	5
2.3	Harmonic driven AC-bridge with voltage amplifier	6
2.4	Switched capacitor circuit	6
2.5	Conventional capacitance-to-voltage converter	8
2.6	modified capacitance-to-voltage converter	8
2.7	First order relaxation oscillator	9
2.8	Cross coupled LC oscillator	10
2.9	Ring oscillator	10
2.10	Leakage power in CMOS: I1 (Diode reverse bias current), I2 (current), I3 (Gate-induced drain leakage), I4 (Gate oxide leakage)	14
2.11	Architecture partition	16
2.12	Pipelined methodology	17
2.13	Concept diagram of clock bootstrapped technique	19
3.1	Cross-section of Intel's Tri-gate	23
3.2	3D view of Intel's Tri-gate device	24
3.3	Width quantization	27
3.4	Top view and cross-sectional schematic of a FinFET device.	28
3.5	The circuit diagram used to simulate DC characteristics for NMOS FinFET	28
3.6	DC characteristics for NMOS FinFET	29
3.7	The circuit diagram used to simulate DC characteristics for PMOS FinFET	29
3.8	DC characteristics for PMOS FinFET	30
3.9	Test-bench for five stages ring oscillator using FinFET	31
3.10	Transient output results for FinFET ring oscillator	31
3.11	Test-bench for five stages ring oscillator using CMOS TSMC 0.13 μm	32

3.12	Transient output results for CMOS TSMC 0.13 μm ring oscillator	32
4.1	System proposed for the readout circuit using NFC approach	33
4.2	The sensor capacitance vs pressure	36
4.3	Cross coupled LC oscillator circuit diagram	37
4.4	LC oscillator circuit design using TSMC 0.13 μm design kit	39
4.5	Output frequency variation in the TSMC 0.13 μm LC oscillator circuit	39
4.6	Transient simulation of the TSMC 0.13 μm LC oscillator	40
4.7	Supply variation in the TSMC 0.13 μm LC oscillator	40
4.8	LC oscillator circuit design using FinFET technology	41
4.9	Output frequency variation in the FinFET LC oscillator circuit	42
4.10	Transient simulation of the FinFET LC oscillator	43
4.11	Supply variation in the FinFET LC oscillator	43
4.12	DC characteristics of UMC 0.13 μm inverter	45
4.13	Schematic diagram of the ring oscillator designed using UMC 0.13 μm	46
4.14	Output frequency variation for the UMC 0.13 μm ring oscillator circuit in the schematic simulation	47
4.15	Transient voltage at sensor driver node for the UMC 0.13 μm ring oscillator in the schematic simulation	48
4.16	Spectrum of transient voltage at sensor driver node for the UMC 0.13 μm ring oscillator in the schematic simulation	48
4.17	Supply variation in the UMC 0.13 μm ring oscillator schematic simulation	49
4.18	Layout of ring oscillator without output pad using UMC 0.13 μm design kit	50
4.19	Layout of ring oscillator with output pad using UMC 0.13 μm design kit	51
4.20	Output frequency variation for the UMC 0.13 μm ring oscillator circuit in the post layout simulation	52
4.21	Transient voltage at sensor driver node for the UMC 0.13 μm ring oscillator circuit in the post layout simulation	52
4.22	Spectrum of transient voltage at sensor driver node for the UMC 0.13 μm ring oscillator in the post layout simulation	53
4.23	Supply variation in the UMC 0.13 μm ring oscillator post layout simulation	53
4.24	Schematic diagram of the ring oscillator designed using FinFET technology	54
4.25	Output frequency variation for FinFET ring oscillator circuit	55

4.26	Transient simulation at the sensor driver node of the FinFET ring oscillator	55
4.27	Spectrum of transient voltage at sensor driver node for the FinFET ring oscillator	56
4.28	Supply variation in the FinFET ring oscillator	56
4.29	Side view of layer stacks for FinFET as given in FreePDK15	58
4.30	Side view of layer stacks for FinFET transistor with one fin as given in FreePDK15	59
4.31	Comparison between inverter areas of FinFET 20 nm and CMOS using UMC 130 nm (UMC=FinFET X64)	59
4.32	Layout of inverter with one fin using FinFET FreePDK15	60
4.33	Schematic diagram of the counter	61
4.34	Schematic diagram of the Flip Flop	62
4.35	Schematic diagram of the register	62
4.36	The relation between gating signal and reset signal in time domain showing the time of output appearance	63
4.37	The reset extraction from the clock signal	63
4.38	Transient simulation for TSMC 0.13 μm counter	65
4.39	Transient simulation for FinFET counter	66
5.1	Schematic of the ring oscillator test-bench	69
5.2	Transient result of the ring oscillator test-bench	69
5.3	Effect of substrate orientation and layout style on electron and hole mobility equalization in FinFET designs	70

List of Tables

3.1	PTM-CMG Parameters	27
4.1	Industrial Scientific Medical (ISM) bands [17]	34
4.2	Geometry parameters for the capacitive pressure sensor	35
4.3	Power dissipated in each block	67

Chapter 1

Introduction

Among the different techniques usually used to reduce power consumption in custom circuits is to replace the conventional CMOS MOSFETs by FinFETs. Basically FinFETs have low leakage current and negligible short channel effects leading to low power consumption.

1.1 Motivation

Down-scaling of MOS devices is continuously attempted aiming to achieve faster circuit speed, smaller area, and lower power dissipation. Multi-gate MOSFET is one of the most promising semiconductor devices that was proven to be the best choice for future ICs, so, it has become an intense subject of scientific research. Sensor application usually don't need high speed, but requires low power consumption which is the most important issue in the design of battery operated ubiquitous applications. In this work the technology route rather than architectural or power management routes has been chosen to design a low power readout circuit for a capacitive pressure sensor.

1.2 Organization

The organization of the thesis is as follows: chapter 1 presents an introduction on the main idea behind this work, chapter 2 introduces a background on the sensor used, architectures for readout circuit, and low power techniques found in the literature. Chapter 3 is devoted to FinFET its advantage, Chapter 4 gives the proposed design of the readout circuit with its simulation. Finally a discussion is given and a conclusion is drawn in chapter 5.